In the Specification

At page 1, before the "Technical Field" section, please insert:

RELATED PATENT DATA

This patent resulted from a continuation-in-part of U.S. Patent Application Serial No. 10/656,732 , which was filed September 4, 2003.

At page 5, please amend paragraph 0019 as follows:

[0019] Fig. 9 is a diagrammatic, cross-sectional view along the line 9-9 of the Fig. 8 fragment, and illustrates a slightly different aspect of the invention than Figs. 7 and 8.

At page 9, please amend paragraph 0045 as follows:

[0045] Various aspects of the invention are described below with reference to Figs. [[1-29]] 1-30.

At pages 17 and 18, please amend paragraph 0065 as follows:

[0065] Fig. 9 shows containers 84 and 86 associated with openings 34 and 50, in addition to the container 64 associated with opening 42. Containers 84 and 86 extend to node locations 85 and 87, which can comprise similar constructions to those described above relative to node location 22. Container constructions 84 and 86 comprise the interior peripheries 70 and outer peripheries 72 described previously with reference to containers 62, 64, 66 and 68 of Fig. 5. In the shown aspect of the invention, masking material 80 extends into openings 34, 42 and 50. Specifically, the masking material extends along the interior lateral surfaces 70 of each of the openings, and in the shown aspect extends

entirely along at least one of the interior lateral surfaces 70 of each of the openings. In typical processing, a sacrificial material (not shown) would be provided in openings 32, 34, 36, 38, 40, 42, 44, 46, 48, 50, 52 and 54 during the above-described chemical-mechanical polishing of layer 60. The sacrificial material can be removed from within the openings at any suitable processing stage, which may be a stage before provision of masking material 80, or a stage after provision of masking material 80. If the sacrificial material remains in the openings during provision of masking material 80, the sacrificial material may preclude material 80 from entering the openings. In such aspects, material 80 may not be along the interior surfaces of the openings, but instead would be over the openings. In some aspects it can be desired to leave the sacrificial material within the openings during provision of masking material 80 to alleviate thinning of material 80 that might otherwise occur, and in other aspects it can be desired to remove the sacrificial material prior to formation of masking material 80. The illustration of Fig. 9 is somewhat inconsistent with Figs. 7 and 8 in that Fig. 9 shows material 80 extending within the opening 42 and Figs. 7 and 8 show opening 42 having a region within which material 80 does not extend. Thus, Fig. 9 illustrates a slightly different aspect of the invention than Figs. 7 and 8.

At page 22, please amend paragraph 0079 as follows:

[0079] Referring next to Figs. 17-19, a dielectric material 100 and a conductive material ~~102~~ 103 are formed within openings 32, 34, 36, 38, 40, 42, 44, 46, 48, 50, 52 and 54, as well as along outer sidewall edges 72 of the container structures. Conductive material 60 of the capacitor container structures can be referred to as a first capacitor electrode, and conductive material ~~102~~ 103 can be referred to as a second capacitor electrode. The capacitor electrodes 60 and ~~102~~ 103, together with dielectric material 100, form an array of capacitor structures within the array of openings 32, 34, 36, 38, 40, 42, 44, 46, 48, 50, 52 and 54. The openings, together with trench 56, are shown in phantom view in Fig. 18 to indicate that such are below conductive material ~~102~~ 103 in the shown view. Although the shown capacitors are container capacitors, it is to be understood that the capacitors can also be pedestal capacitors (i.e., can comprise the dielectric material 100 and the conductive material ~~102~~ 103 extending around pedestals of material 60) in accordance with various aspects of the invention discussed above.

At page 23, please amend paragraph 0080 as follows:

[0080] It can be preferred that retaining structure 30 consist of electrically insulative materials so that the retaining structure can remain in construction 10 (as shown in Figs. 17-19), without shorting between capacitor container structures in physical contact with retaining structure 30. However, it is to be understood that the invention can encompass other aspects (not shown) in which structure 30 is removed after formation of one or both of dielectric material 100 and second capacitor electrode 102; and in such aspects retaining structure 30 can comprise electrically conductive materials in addition to, or alternatively to, electrically insulative materials. Retaining structure can be removed after formation of one or both of dielectric material 100 and second capacitor electrode 102 since the dielectric material and second capacitor electrode can each provide structural stability to the container structures (such as, for example, structures 62, 64, 66 and 68 of Fig. 14), so that the container structures can be supported without retaining structure 30. In aspects in which retaining structure 30 is to be removed, such can be accomplished utilizing, for example, photolithographic patterning to form a mask (not shown), followed by an appropriate etch, or etches, to penetrate any materials over retaining structure 30 and subsequently remove retaining structure 30.

At page 28, please amend paragraph 0094 as follows:

[0094] Referring to Fig. 25, a construction 500 is illustrated at the processing step described previously with reference to Fig. 1. Construction 500 is similar to the construction 10 described in Fig. 1, except that the material 30 of Fig. ~~500~~ 25 is illustrated comprising two separate layers 502 and 504. One of layers 502 and 504 can, in particular aspects of the invention, comprise, consist essentially of, or consist of silicon nitride. The other of layers 502 and 504 can, in particular aspects of the invention, comprise, consist essentially of, or consist of silicon, and can be in the form of, for example, amorphous silicon and/or polycrystalline silicon.